TOSHIBA Field Effect Transistor Silicon N Channel MOS Type

SSM3K02T

High Speed Switching Applications

Unit: mm

2.8+0.2

1.6+0.2

1. GATE 2. SOURCE 3. DRAIN

1.9±0.2

TSM

JEDEC JEITA

Small package

Low on resistance: $R_{on} = 200 \text{ m}\Omega \text{ (max) (V}_{GS} = 4 \text{ V)}$: $R_{on} = 250 \text{ m}\Omega \text{ (max) (V}_{GS} = 2.5 \text{ V)}$

Low gate threshold voltage: $V_{th} = 0.6 \sim 1.1 \text{ V (VDS} = 3 \text{ V, ID} = 0.1 \text{ mA)}$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	
Drain-source voltage		V_{DS}	30	V	
Gate-source voltage		V _{GSS}	±10	V	
Drain current	DC	ID	2.5	А	
	Pulse	I _{DP}	5.0		
Drain power dissipation (Ta = 25°C)		P _D (Note 1)	1250	mW	
Channel temperature		T _{ch}	150	°C	
Storage temperature range		T _{stg}	−55~150	°C	

Using continuously under heavy loads (e.g. the application of

TOSHIBA 2-3S1A Weight: 0.01 g (typ.)

high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

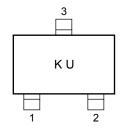
Note 1: Mounted on FR4 board

 $(25.4 \text{ mm} \times 25.4 \text{ mm} \times 1.6 \text{ t}, \text{ Cu pad: } 645 \text{ mm}^2, \text{ t} = 10 \text{ s})$

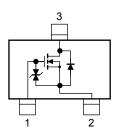
Note 2: The pulse width limited by max channel temperature.

Marking

Note:



Equivalent Circuit



Handling Precaution

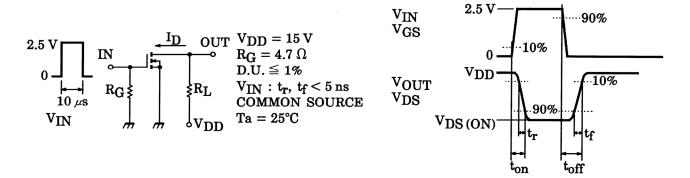
When handling individual devices (which are not yet mounted on a circuit board), be sure that the environment is protected against electrostatic electricity. Operators should wear anti-static clothing, and containers and other objects that come into direct contact with devices should be made of anti-static materials.

Electrical Characteristics (Ta = 25°C)

Chara	acteristics	Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current		I _{GSS}	$V_{GS} = \pm 10 \text{ V}, V_{DS} = 0$		_	_	±5	μΑ
Drain-source brea	source breakdown voltage V (BR) DSS I _D = 1 mA, V _{GS} = 0			30	_	_	V	
$\label{eq:Drain} \mbox{Drain cut-off current} \qquad \qquad \mbox{I}_{DSS} \qquad \mbox{V}_{DS} = 30 \mbox{ V},$		V _{DS} = 30 V, V _{GS} = 0		_	_	1	μА	
Gate threshold vo	oltage	V _{th}	$V_{DS} = 3 \text{ V}, I_D = 0.1 \text{ mA}$		0.6	_	1.1	V
Forward transfer	admittance	Y _{fs}	V _{DS} = 3 V, I _D = 1.25 A	(Note)	2.2	_	_	S
Drain-source ON resistance		R _{DS (ON)}	I _D = 1.25 A, V _{GS} = 4 V	(Note)	_	140	200	mΩ
			I _D = 1.25 A, V _{GS} = 2.5 V	(Note)	_	180	250	
Input capacitance	•	C _{iss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		_	115	_	pF
Reverse transfer capacitance		C _{rss}	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		_	24	_	pF
Output capacitance		Coss	V _{DS} = 10 V, V _{GS} = 0, f = 1 MHz		_	60	_	pF
Switching time	Turn-on time	t _{on}	$V_{DD} = 15 \text{ V}, I_{D} = 0.5 \text{ A}, V_{GS} = 0~2.5 \text{ V}, R_{G} = 4.7 \Omega$		_	52	_	20
	Turn-off time	t _{off}		_	80	_	ns	

Note: Pulse test

Switching Time Test Circuit

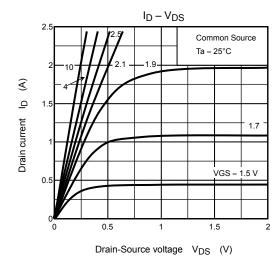


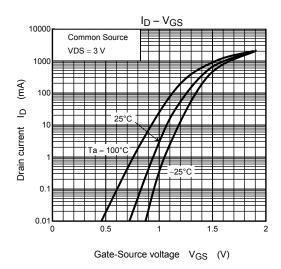
Precaution

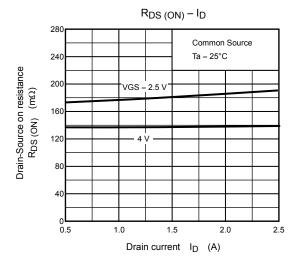
 V_{th} can be expressed as voltage between gate and source when low operating current value is ID = 100 μ A for this product. For normal switching operation, VGS (ON) requires higher voltage than V_{th} and VGS (off) requires lower voltage than V_{th} .

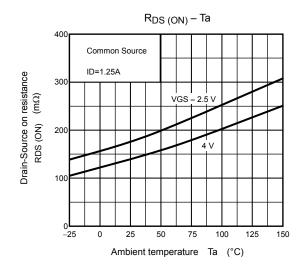
(Relationship can be established as follows: V_{GS} (off) $< V_{th} < V_{GS}$ (ON))

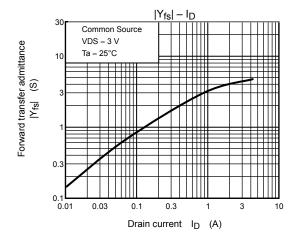
Please take this into consideration for using the device.

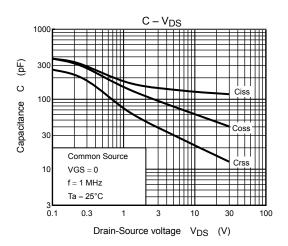






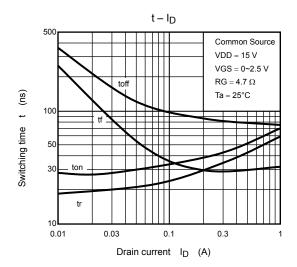


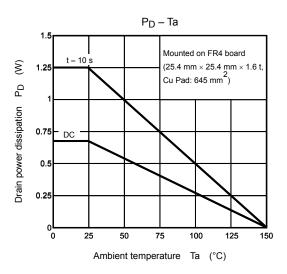


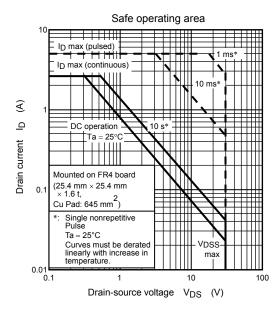


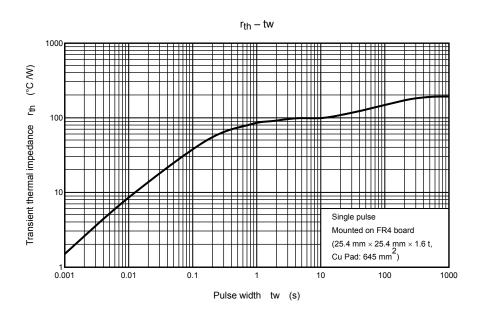
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20070701-EN GENERAL

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